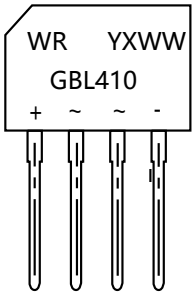
WRGBL410

23-NOV-2017

Ultrasoft Recovery Bridge



Features

- Glass Passivated Chip Junction
- Reverse Voltage - 1000 V
- Forward Current - 4 A
- High Surge Current Capability
- Designed For Surface Mount Application

PINNING

PIN	DESCRIPTION
1	Input Pin（~）
2	Input Pin（~）
3	Output Anode（+）
4	Output Cathode（-）

Benefits

- Case: GBL
- Terminals: Solderable Per MIL-STD-750

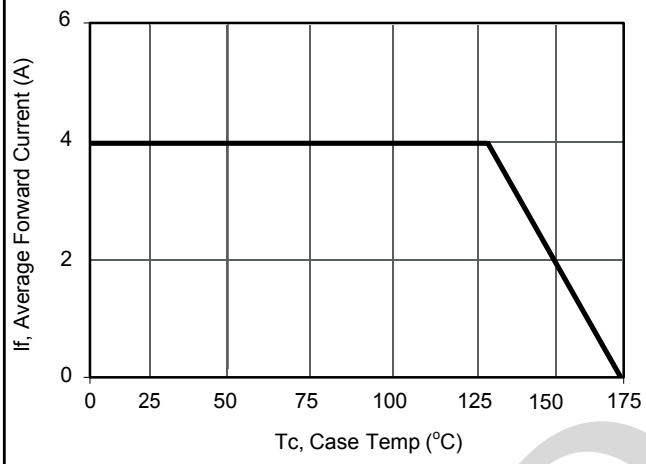
Maximum Ratings and Electrical characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

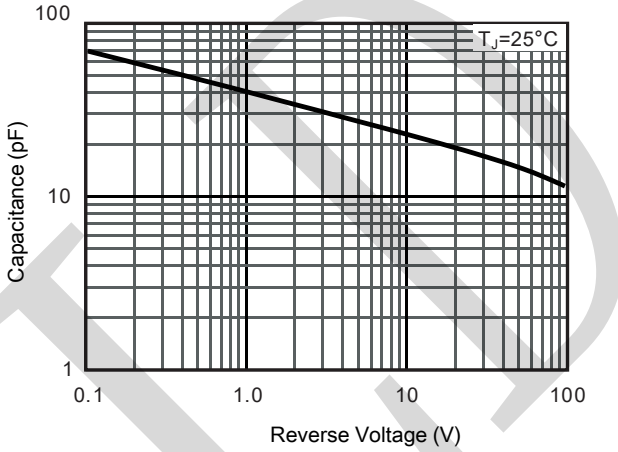
Parameter	Symbols	WRGBL410	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	1000	V
Maximum RMS voltage	V_{RMS}	700	V
Maximum DC Blocking Voltage	V_{DC}	1000	V
Average Rectified Output Current	I_o	4.0	A
Reverse Recovery Time. IF=0.5A,IR=1A,IRR=0.25A	Trr	10	us
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	110	A
I^2t rating for fusing (1ms< t < 10ms)	I^2t	93	A^2S
Maximum Forward Voltage at 2.0 A	V_F	1.0	V
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	I_R	5 100	μA
Typical Junction Capacitance（Note1）	C_j	50	pF
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +175	°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.

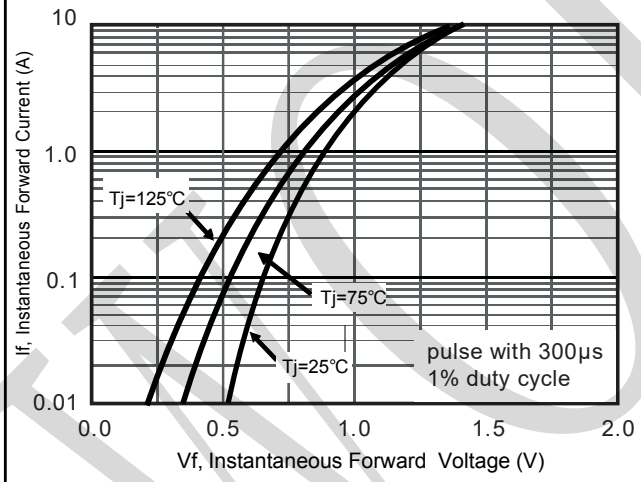
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



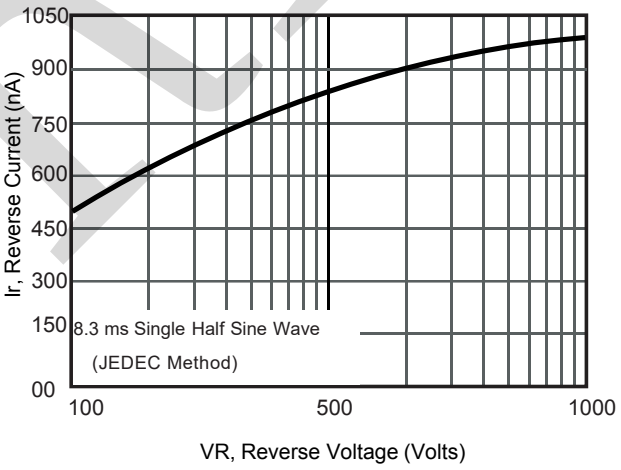
Current Derating, Case



Typical Junction Capacitance



Typical Forward Voltage



Typical Reverse Current

PACKAGE OUTLINE DIMENSIONS